

Detlev A GrÃ¼tzmacher

List of Publications by Year in descending order

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315
papers

8,852
citations

50170

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322
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322
docs citations

322
times ranked

7265
citing authors

#	ARTICLE	IF	CITATIONS
1	High speed imaging of Z-pinch gas discharge in extreme ultraviolet and model-based three-dimensional reconstruction of emitting volume. Review of Scientific Instruments, 2022, 93, 013503.	0.6	3
2	Te-doped selective-area grown InAs nanowires for superconducting hybrid devices. Physical Review Materials, 2022, 6, .	0.9	1
3	Gate-induced decoupling of surface and bulk state properties in selectively-deposited Bi ₂ Te ₃ nanoribbons. SciPost Physics Core, 2022, 5, .	0.9	8
4	NEUROTEC I: Neuro-inspired Artificial Intelligence Technologies for the Electronics of the Future. , 2022, , .		0
5	Fully <i>in situ</i> Nb/InAs-nanowire Josephson junctions by selective-area growth and shadow evaporation. Nanoscale Advances, 2021, 3, 1413-1421.	2.2	11
6	Flux periodic oscillations and phase-coherent transport in GeTe nanowire-based devices. Nature Communications, 2021, 12, 754.	5.8	6
7	Reappearance of first Shapiro step in narrow topological Josephson junctions. Science Advances, 2021, 7, .	4.7	14
8	Lifting the Spin-Momentum Locking in Ultra-Thin Topological Insulator Films. Advanced Quantum Technologies, 2021, 4, 2100083.	1.8	6
9	In-plane magnetic field-driven symmetry breaking in topological insulator-based three-terminal junctions. Communications Materials, 2021, 2, .	2.9	5
10	Quantum Transport in Topological Surface States of Selectively Grown Bi ₂ Te ₃ Nanoribbons. Advanced Electronic Materials, 2020, 6, 2000205.	2.6	21
11	Phase-Pure Wurtzite GaAs Nanowires Grown by Self-Catalyzed Selective Area Molecular Beam Epitaxy for Advanced Laser Devices and Quantum Disks. ACS Applied Nano Materials, 2020, 3, 11037-11047.	2.4	10
12	Hard-Gap Spectroscopy in a Self-Defined Mesoscopic $\ln_{x}\text{As}_{1-x}$ Nanowire Josephson Junction. Physical Review Applied, 2020, 14, .	1.5	4
13	Proximity-Induced Superconductivity in Nb/Sb ₂ Te ₃ Nanoribbon/Nb Junctions. Annalen Der Physik, 2020, 532, 2000273.	0.9	5
14	Room temperature in-situ measurement of the spin voltage of a BiSbTe ₃ thin film. Scientific Reports, 2020, 10, 2816.	1.6	9
15	Phase-coherent loops in selectively-grown topological insulator nanoribbons. Nanotechnology, 2020, 31, 325001.	1.3	12
16	Phase coherent transport and spin-orbit interaction in GaAs/InSb core/shell nanowires. Semiconductor Science and Technology, 2020, 35, 085003.	1.0	5
17	Selective area growth and stencil lithography for in situ fabricated quantum devices. Nature Nanotechnology, 2019, 14, 825-831.	15.6	70
18	Influence of Te-Doping on Catalyst-Free VS InAs Nanowires. Nanoscale Research Letters, 2019, 14, 179.	3.1	4

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19	Signatures of induced superconductivity in AlOx-capped topological heterostructures. Solid-State Electronics, 2019, 155, 111-116.	0.8	4
20	Phase-coherent transport in selectively grown topological insulator nanodots. Nanotechnology, 2019, 30, 055201.	1.3	6
21	Quantum interferometer based on GaAs/InAs core/shell nanowires connected to superconducting contacts. Semiconductor Science and Technology, 2018, 33, 064001.	1.0	4
22	Advanced GeSn/SiGeSn Group IV Heterostructure Lasers. Advanced Science, 2018, 5, 1700955.	5.6	61
23	In situ disentangling surface state transport channels of a topological insulator thin film by gating. Npj Quantum Materials, 2018, 3, .	1.8	14
24	Nanoscale Near-Field Tomography of Surface States on (Bi _{0.5} Sb _{0.5}) ₂ Te ₃ . Nano Letters, 2018, 18, 7515-7523.	4.5	50
25	Infrared/terahertz spectra of the photogalvanic effect in (Bi,Sb)Te based three-dimensional topological insulators. Physical Review Materials, 2018, 2, .	0.9	29
26	SiGeSn Ternaries for Efficient Group IV Heterostructure Light Emitters. Small, 2017, 13, 1603321.	5.2	40
27	Magnetoresistance oscillations in MBE-grown Sb ₂ Te ₃ thin films. Applied Physics Letters, 2017, 110, .	1.5	13
28	BiTe ₁ is a dual topological insulator. Nature Communications, 2017, 8, 14976.	5.8	66
29	Stencil lithography of superconducting contacts on MBE-grown topological insulator thin films. Journal of Crystal Growth, 2017, 477, 183-187.	0.7	13
30	Signatures of interaction-induced helical gaps in nanowire quantum point contacts. Nature Physics, 2017, 13, 563-567.	6.5	77
31	Electron Interference in Hall Effect Measurements on GaAs/InAs Core/Shell Nanowires. Nano Letters, 2017, 17, 128-135.	4.5	10
32	MBE growth of Al/InAs and Nb/InAs superconducting hybrid nanowire structures. Nanoscale, 2017, 9, 16735-16741.	2.8	22
33	Nano-Angle Resolved Photoemission Spectroscopy on Topological insulator Sb ₂ Te ₃ nanowires responsible of quantum transport. Journal of Physics: Conference Series, 2017, 864, 012041.	0.3	3
34	Anisotropic phase coherence in GaAs/InAs core/shell nanowires. Nanotechnology, 2017, 28, 445202.	1.3	3
35	Electrical resistance of individual defects at a topological insulator surface. Nature Communications, 2017, 8, 15704.	5.8	29
36	Strain relaxation and ambipolar electrical transport in GaAs/InSb core-shell nanowires. Nanoscale, 2017, 9, 18392-18401.	2.8	10

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37	Chalcogenide-based van der Waals epitaxy: Interface conductivity of tellurium on Si(111). Physical Review B, 2017, 96, .	1.1	12
38	Electronic Properties of Complex Self-Assembled InAs Nanowire Networks. Advanced Electronic Materials, 2016, 2, 1500460.	2.6	10
39	Nano-light-emitting-diodes based on InGaN mesoscopic structures for energy saving optoelectronics. Applied Physics Letters, 2016, 109, .	1.5	23
40	Band bending at the heterointerface of GaAs/InAs core/shell nanowires monitored by synchrotron X-ray photoelectron spectroscopy. Journal of Applied Physics, 2016, 120, 145703.	1.1	7
41	Electrical and optical characterization of freestanding Ge _{1-x} Sb _{2-x} Te _{4-x} nano-membranes integrated in coplanar strip lines. , 2016, , .		8
42	Direct electro-optical pumping for hybrid CdSe nanocrystal/III-nitride based nano-light-emitting diodes. Applied Physics Letters, 2016, 108, 061107.	1.5	38
43	Quantum Transport and Nano Angle-resolved Photoemission Spectroscopy on the Topological Surface States of Single Sb ₂ Te ₃ Nanowires. Scientific Reports, 2016, 6, 29493.	1.6	43
44	Opto-electronic characterization of three dimensional topological insulators. Journal of Applied Physics, 2016, 120, .	1.1	25
45	InGaN mesoscopic structures for low energy consumption nano-opto-electronics. , 2016, , .		1
46	Ballistic Transport and Exchange Interaction in InAs Nanowire Quantum Point Contacts. Nano Letters, 2016, 16, 3116-3123.	4.5	46
47	Dense, Regular GaAs Nanowire Arrays by Catalyst-Free Vapor Phase Epitaxy for Light Harvesting. ACS Applied Materials & Interfaces, 2016, 8, 22484-22492.	4.0	2
48	Topography and structure of ultrathin topological insulator Sb ₂ Te ₃ films on Si(111) grown by means of molecular beam epitaxy. Journal of Crystal Growth, 2016, 453, 158-162.	0.7	20
49	Photon drag effect in Bi_2Te_3 topological insulators. Physical Review B. 2016, 93, .		9
50	Adiabatic Edge Channel Transport in a Nanowire Quantum Point Contact Register. Nano Letters, 2016, 16, 4569-4575.	4.5	24
51	Growth, characterization, and transport properties of ternary $(\text{Bi}_{1-x}\text{Sb}_x)_2\text{Te}_{3-x}$ topological insulator layers. Journal of Physics Condensed Matter, 2016, 28, 495501.	0.7	41
52	Low-energy consumption nano-opto-electronics based on III-nitride-LED mesoscopic structures. , 2016, , .		0
53	Angle-dependent magnetotransport in GaAs/InAs core/shell nanowires. Scientific Reports, 2016, 6, 24573.	1.6	10
54	Optically Pumped GeSn Microdisk Lasers on Si. ACS Photonics, 2016, 3, 1279-1285.	3.2	195

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55	Selective area growth of Bi ₂ Te ₃ and Sb ₂ Te ₃ topological insulator thin films. Journal of Crystal Growth, 2016, 443, 38-42.	0.7	32
56	P ⁿ Junctions in Ultrathin Topological Insulator Sb ₂ Te ₃ /Bi ₂ Te ₃ Heterostructures Grown by Molecular Beam Epitaxy. Crystal Growth and Design, 2016, 16, 2057-2061.	1.4	36
57	Crystal Phase Transformation in Self-Assembled InAs Nanowire Junctions on Patterned Si Substrates. Nano Letters, 2016, 16, 1933-1941.	4.5	26
58	Tuning the Dirac point to the Fermi level in the ternary topological insulator (Bi _{1-x} Sb _x) ₂ Te ₃ . Applied Physics Letters, 2015, 107, .	1.5	40
59	Coherent ultrafast spin-dynamics probed in three dimensional topological insulators. Scientific Reports, 2015, 5, 15304.	1.6	16
60	InAs nanowires with Al Ga _{1-x} Sb shells for band alignment engineering. Journal of Crystal Growth, 2015, 425, 80-84.	0.7	7
61	Realization of a vertical topological p ⁿ junction in epitaxial Sb ₂ Te ₃ /Bi ₂ Te ₃ heterostructures. Nature Communications, 2015, 6, 8816.	5.8	85
62	Suppressing Twin Domains in Molecular Beam Epitaxy Grown Bi ₂ Te ₃ Topological Insulator Thin Films. Crystal Growth and Design, 2015, 15, 390-394.	1.4	59
63	Simultaneous Integration of Different Nanowires on Single Textured Si (100) Substrates. Nano Letters, 2015, 15, 1979-1986.	4.5	8
64	Lasing in direct-bandgap GeSn alloy grown on Si. Nature Photonics, 2015, 9, 88-92.	15.6	1,016
65	SiGe quantum dot crystals with periods down to 35 nm. Nanotechnology, 2015, 26, 255302.	1.3	12
66	Resolving ambiguities in nanowire field-effect transistor characterization. Nanoscale, 2015, 7, 18188-18197.	2.8	29
67	Optical Transitions in Direct-Bandgap Ge _{1-x} Sn _x Alloys. ACS Photonics, 2015, 2, 1539-1545.	3.2	83
68	Misfit dislocation free InAs/GaSb core-shell nanowires grown by molecular beam epitaxy. Nanoscale, 2015, 7, 356-364.	2.8	42
69	Direct bandgap GeSn alloys for laser application. , 2015, , .		0
70	Epitaxy and photoluminescence studies of high quality GeSn heterostructures with Sn concentrations up to 13 at.%. , 2014, , .		1
71	III-nitride nano-LEDs for single photon lithography. , 2014, , .		1
72	Templates for highly ordered SiGe-QD arrays for single photon detection. , 2014, , .		0

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73	Phase coherent transport in hollow InAs nanowires. Applied Physics Letters, 2014, 105, 113111.	1.5	6
74	Flux periodic magnetoconductance oscillations in GaAs/InAs core/shell nanowires. Physical Review B, 2014, 89, .	1.1	47
75	Generation of circularly polarized radiation from a compact plasma-based extreme ultraviolet light source for tabletop X-ray magnetic circular dichroism studies. Review of Scientific Instruments, 2014, 85, 103110.	0.6	15
76	Spin injection and spin-orbit coupling in low-dimensional semiconductor nanostructures. , 2014, , .		0
77	Quantum dots in InAs nanowires induced by surface potential fluctuations. Nanotechnology, 2014, 25, 135203.	1.3	7
78	Impact of thermal annealing on nonequilibrium carrier dynamics in single-crystal, freestanding GaAs mesostructures. Semiconductor Science and Technology, 2014, 29, 045022.	1.0	8
79	SiGeSn growth studies using reduced pressure chemical vapor deposition towards optoelectronic applications. Thin Solid Films, 2014, 557, 183-187.	0.8	48
80	Evolution and characteristics of GaN nanowires produced via maskless reactive ion etching. Nanotechnology, 2014, 25, 255301.	1.3	10
81	Giant Magnetoconductance Oscillations in Hybrid Superconductor~Semiconductor Core/Shell Nanowire Devices. Nano Letters, 2014, 14, 6269-6274.	4.5	17
82	Crystal Phase Selective Growth in GaAs/InAs Core~Shell Nanowires. Crystal Growth and Design, 2014, 14, 1167-1174.	1.4	27
83	Room-Temperature High-Frequency Transport of Dirac Fermions in Epitaxially Grown Sb_2Bi and Bi . Physical Review Letters, 2014, 113, 096601.	2.9	101
84	Crossover from Josephson Effect to Single Interface Andreev Reflection in Asymmetric Superconductor/Nanowire Junctions. Nano Letters, 2014, 14, 4977-4981.	4.5	24
85	Generation of THz transients by photoexcited single-crystal GaAs meso-structures. Applied Physics B: Lasers and Optics, 2013, 113, 339-344.	1.1	2
86	Self-catalyzed VLS grown InAs nanowires with twinning superlattices. Nanotechnology, 2013, 24, 335601.	1.3	56
87	Tensely strained GeSn alloys as optical gain media. Applied Physics Letters, 2013, 103, .	1.5	63
88	Si substrate preparation for the VS and VLS growth of InAs nanowires. Physica Status Solidi - Rapid Research Letters, 2013, 7, 840-844.	1.2	20
89	Site-controlled growth of indium nitride based nanostructures using metalorganic vapour phase epitaxy. Journal of Crystal Growth, 2013, 370, 336-341.	0.7	17
90	Controlled wurtzite inclusions in self-catalyzed zinc blende III~V semiconductor nanowires. Journal of Crystal Growth, 2013, 378, 506-510.	0.7	30

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91	Spin polarization limit in Bi ₂ Te ₃ Dirac cone studied by angle- and spin-resolved photoemission experiments and <i>ab initio</i> calculations. <i>Physical Review B</i> , 2013, 87, .	1.1	35
92	Electronic structure, surface morphology, and topologically protected surface states of Sb ₂ Te ₃ thin films grown on Si(111). <i>Journal of Applied Physics</i> , 2013, 113, .	1.1	45
93	Nanoimprint and selective-area MOVPE for growth of GaAs/InAs core/shell nanowires. <i>Nanotechnology</i> , 2013, 24, 085603.	1.3	45
94	Band engineering and growth of tensile strained Ge/(Si)GeSn heterostructures for tunnel field effect transistors. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	131
95	Charge accumulation on the surface of GaAs nanowires near the Schottky contact. <i>Technical Physics Letters</i> , 2013, 39, 209-212.	0.2	2
96	From conformal overgrowth to lateral growth of indium arsenide nano structures on silicon substrates by MOVPE. <i>Journal of Crystal Growth</i> , 2013, 370, 141-145.	0.7	5
97	Gate-induced transition between metal-type and thermally activated transport in self-catalyzed MBE-grown InAs nanowires. <i>Nanotechnology</i> , 2013, 24, 325201.	1.3	4
98	Vertically integrated (Ga, In)N nanostructures for future single photon emitters operating in the telecommunication wavelength range. <i>Nanotechnology</i> , 2013, 24, 405302.	1.3	9
99	Realization of nanoscaled tubular conductors by means of GaAs/InAs core/shell nanowires. <i>Nanotechnology</i> , 2013, 24, 035203.	1.3	43
100	Spectral Sensitivity Tuning of Vertical InN Nanopyramid-Based Photodetectors. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JF05.	0.8	12
101	Axial strain in GaAs/InAs core-shell nanowires. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	31
102	Domain formation due to surface steps in topological insulator Bi ₂ Te ₃ thin films grown on Si (111) by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	22
103	Highly Transparent Conducting Polymer Top Contacts for Future III-V Nitride Based Single Photon Emitters. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JH10.	0.8	6
104	Reduced Pressure CVD Growth of Ge and Ge _{1-x} Sn _x Alloys. <i>ECS Journal of Solid State Science and Technology</i> , 2013, 2, N99-N102.	0.9	67
105	FLUX QUANTUM OSCILLATIONS IN GaAs/InAs CORE/SHELL NANOWIRES. , 2013, , .		0
106	Photoluminescence and Raman scattering studies of GaN nanowires obtained by top-down and bottom-up approaches. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1408, 29.	0.1	2
107	Supercurrent in Nb/InAs-nanowire/Nb Josephson junctions. <i>Journal of Applied Physics</i> , 2012, 112, .	1.1	43
108	Subpicosecond electron-hole recombination time and terahertz-bandwidth photoresponse in freestanding GaAs epitaxial mesoscopic structures. <i>Applied Physics Letters</i> , 2012, 101, .	1.5	15

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109	Phase coherent transport in InSb nanowires. Applied Physics Letters, 2012, 101, 082103.	1.5	15
110	Non-uniform distribution of induced strain in a gate-recessed AlGaIn/GaN structure evaluated by micro-PL measurements. Semiconductor Science and Technology, 2012, 27, 105008.	1.0	14
111	Preparation of Ohmic contacts to GaAs/AlGaAs-core/shell-nanowires. Applied Physics Letters, 2012, 100, .	1.5	16
112	Electrical Spin Injection into InN Semiconductor Nanowires. Nano Letters, 2012, 12, 4437-4443.	4.5	36
113	Optimized marker definition for high overlay accuracy e-beam lithography. Microelectronic Engineering, 2012, 97, 68-71.	1.1	8
114	The d-DotFET: MOSFET based on locally strained silicon. , 2012, , .		0
115	Towards future III-nitride based THz OEICs in the UV range. , 2012, , .		0
116	Tuning the spectral sensitivity of vertical InN nanopillar based photodetectors by means of band gap engineering and/or nanostructure size control. , 2012, , .		0
117	Hall effect measurements on InAs nanowires. Applied Physics Letters, 2012, 101, 152106.	1.5	88
118	Ga-assisted MBE growth of GaAs nanowires using thin HSQ layer. Journal of Crystal Growth, 2012, 353, 39-46.	0.7	71
119	Thermally Oxidized InAlN of Different Compositions for InAlN/GaN Heterostructure Field-Effect Transistors. Journal of Electronic Materials, 2012, 41, 3013-3016.	1.0	4
120	GaAs nanowhiskers for femtosecond photodetectors and THz emitters. , 2012, , .		0
121	Mode of Growth of Ultrathin Topological Insulator Bi ₂ Te ₃ Films on Si (111) Substrates. Crystal Growth and Design, 2012, 12, 6098-6103.	1.4	62
122	Molecular Beam Epitaxy Growth of GaAs/InAs Core-Shell Nanowires and Fabrication of InAs Nanotubes. Nano Letters, 2012, 12, 5559-5564.	4.5	71
123	Comparison of InAs nanowire conductivity: influence of growth method and structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 230-234.	0.8	8
124	Self-assembled GaN nanostructures by dry etching and their optical properties. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 443-446.	0.8	6
125	Residual strain in recessed AlGaIn/GaN heterostructure field-effect transistors evaluated by micro photoluminescence measurements. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 911-914.	0.8	6
126	Morphology evolution and optical properties of GaN nanopillars grown by selective area MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 624-627.	0.8	5

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127	Core-shell CdTe/TiO ₂ nanostructured solar cell. Journal of Materials Chemistry, 2012, 22, 10441.	6.7	23
128	Electronic Transport with Dielectric Confinement in Degenerate InN Nanowires. Nano Letters, 2012, 12, 2768-2772.	4.5	23
129	Broadband transmission masks, gratings and filters for extreme ultraviolet and soft X-ray lithography. Thin Solid Films, 2012, 520, 5080-5085.	0.8	30
130	Electrical and structural characterization of AlGaIn/GaN field-effect transistors with recessed gate. Vacuum, 2012, 86, 754-756.	1.6	6
131	Field effect transistor based on single crystalline InSb nanowire. Journal of Materials Chemistry, 2011, 21, 2459.	6.7	54
132	Monolithic Integration of Ultrafast Photodetector and MESFET in the GaN Material System. IEEE Photonics Technology Letters, 2011, 23, 1189-1191.	1.3	14
133	Structural and optical properties of InGaIn/GaN nanowire heterostructures grown by molecular beam epitaxy. Journal of Applied Physics, 2011, 109, 014309.	1.1	25
134	Manipulating InAs nanowires with submicrometer precision. Review of Scientific Instruments, 2011, 82, 113705.	0.6	30
135	X-ray Nanodiffraction on a Single SiGe Quantum Dot inside a Functioning Field-Effect Transistor. Nano Letters, 2011, 11, 2875-2880.	4.5	65
136	Effect of Si-doping on InAs nanowire transport and morphology. Journal of Applied Physics, 2011, 110, .	1.1	61
137	Robust surface electronic properties of topological insulators: Bi ₂ Te ₃ films grown by molecular beam epitaxy. Applied Physics Letters, 2011, 98, 222503.	1.5	56
138	Electrical properties of rolled-up p-type Si/SiGe heterostructures. Applied Physics Letters, 2011, 98, .	1.5	6
139	Electronic Phase Coherence in InAs Nanowires. Nano Letters, 2011, 11, 3550-3556.	4.5	68
140	Enhanced Raman Scattering of Ultramarine on Au-coated Ge/Si-nanostructures. Plasmonics, 2011, 6, 413-418.	1.8	19
141	Etching titanium nitride gate stacked on high- ϵ_r dielectric. Microelectronic Engineering, 2011, 88, 2541-2543.	1.1	4
142	MBE growth optimization of topological insulator Bi ₂ Te ₃ films. Journal of Crystal Growth, 2011, 324, 115-118.	0.7	90
143	Integration of MOSFETs with SiGe dots as stressor material. Solid-State Electronics, 2011, 60, 75-83.	0.8	12
144	Tensile strained SiGe quantum well infrared photodetectors based on a light-hole ground state. Applied Physics Letters, 2011, 98, .	1.5	17

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145	MOVPE of n-doped GaAs and modulation doped GaAs/AlGaAs nanowires. Journal of Crystal Growth, 2010, 312, 635-640.	0.7	37
146	Influence of the epitaxial growth and device processing on the overlay accuracy during processing of the d-DotFET. Thin Solid Films, 2010, 518, 2565-2568.	0.8	1
147	Quantum transport in narrow-gap semiconductor nanocolumns. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 386-389.	0.8	5
148	MOSFETs on self-assembled SiGe dots with strain-enhanced mobility. , 2010, , .		0
149	InAlN/GaN/Si heterostructures and field-effect transistors with lattice matched and tensely or compressively strained InAlN. Applied Physics Letters, 2010, 97, 173505.	1.5	19
150	Three-dimensional phononic nanocrystal composed of ordered quantum dots. Applied Physics Letters, 2010, 96, .	1.5	23
151	Single photon detection by means of SiGe-quantum dot arrays. , 2010, , .		1
152	Quantum phenomena during electron transport in InAs nanowires. , 2010, , .		0
153	Femtosecond and highly sensitive GaAs metal-semiconductor-metal photodetectors grown on aluminum mirrors/pseudo-substrates. Semiconductor Science and Technology, 2010, 25, 075001.	1.0	16
154	Titania-assisted electron-beam and synchrotron lithography. Nanotechnology, 2010, 21, 315301.	1.3	5
155	Enhanced light scattering of the forbidden longitudinal optical phonon mode studied by micro-Raman spectroscopy on single InN nanowires. Nanotechnology, 2010, 21, 315702.	1.3	20
156	Quantum confinement effects in Si/Ge heterostructures with spatially ordered arrays of self-assembled quantum dots. Applied Physics Letters, 2010, 96, .	1.5	7
157	Spin-orbit coupling and phase coherence in InAs nanowires. Physical Review B, 2010, 82, .	1.1	79
158	Comparison of AlGaIn/GaN HFETs and MOSHFETs in prospect of oscillator design. , 2010, , .		0
159	Bandgap Characteristics of a 3D Phononic Meta Material Composed of Ordered Quantum Dots. IUTAM Symposium on Cellular, Molecular and Tissue Mechanics, 2010, , 201-208.	0.1	0
160	Evolution and stability of ordered SiGe islands grown on patterned Si(100) substrates. Journal of Applied Physics, 2009, 105, .	1.1	19
161	SiGe quantum well infrared photodetectors on pseudosubstrate. Applied Physics Letters, 2009, 94, .	1.5	16
162	Continuous Voltage Tunability of Intersubband Relaxation Times in Coupled SiGe Quantum Well Structures Using Ultrafast Spectroscopy. Physical Review Letters, 2009, 102, 147401.	2.9	9

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163	Femtosecond electro-optic effect in (Cd,Mn)Te single crystals. Journal of Physics: Conference Series, 2009, 193, 012057.	0.3	1
164	Characterization of AlGaIn/GaN MISHFETs on a Si substrate by static and high-frequency measurements. Semiconductor Science and Technology, 2009, 24, 075014.	1.0	10
165	Growth of Ge dots on templated Si substrates with diffusion-altered holes. Europhysics Letters, 2009, 85, 58002.	0.7	4
166	Raman scattering of phonon-plasmon coupled modes in self-assembled GaN nanowires. Journal of Applied Physics, 2009, 105, .	1.1	91
167	Interdiffusion in Ge rich SiGe/Ge multilayers studied by <i>in situ</i> diffraction. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1775-1779.	0.8	10
168	Study on growth and electrical performance of double-heterostructure AlGaIn/GaN/AlGaIn field-effect transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1003.	0.8	6
169	Influence of growth temperature on the selective area MOVPE of InAs nanowires on GaAs (111) B using N ₂ carrier gas. Journal of Crystal Growth, 2009, 311, 3813-3816.	0.7	36
170	Influence of growth temperature on GaN:Cr incorporation and structural properties in MOVPE. Journal of Crystal Growth, 2009, 312, 1-9.	0.7	9
171	Output Power Improvement in MSM Photomixers by Modified Finger Contacts Configuration. IEEE Photonics Technology Letters, 2009, 21, 146-148.	1.3	9
172	X-ray diffraction investigation of a three-dimensional Si/SiGe quantum dot crystal. Physical Review B, 2009, 79, .	1.1	25
173	3D SiGe QUANTUM DOT CRYSTALS: STRUCTURAL CHARACTERIZATION AND ELECTRONIC COUPLING. International Journal of Modern Physics B, 2009, 23, 2836-2841.	1.0	5
174	The disposable dot FET: A strained silicon channel on top of removed SiGe. , 2009, , .		3
175	Interface and Wetting Layer Effect on the Catalyst-Free Nucleation and Growth of GaN Nanowires. Small, 2008, 4, 751-754.	5.2	145
176	Interdiffusion in SiGe alloys with Ge contents of 25% and 50% studied by X-ray reflectivity. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2441-2448.	0.8	4
177	Ultra flexible SiGe/Si/Cr nanosprings. Microelectronics Journal, 2008, 39, 478-481.	1.1	24
178	Sensitivity Enhancement of Metal-Semiconductor-Metal Photodetectors on Low-Temperature-Grown GaAs Using Alloyed Contacts. IEEE Photonics Technology Letters, 2008, 20, 1054-1056.	1.3	16
179	Photoluminescence studies of SiGe quantum dot arrays prepared by templated self-assembly. Europhysics Letters, 2008, 84, 67017.	0.7	25
180	Modulation-doped Si _x Ge _{1-x} /Si shells electrically isolated from conductive substrates. Semiconductor Science and Technology, 2008, 23, 105007.	1.0	6

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182	Directed batch assembly of three-dimensional helical nanobelts through angular winding and electroplating. Nanotechnology, 2007, 18, 055304.	1.3	17
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